

# OKI electronic components

## KGF1284

### Power FET (Plastic Package Type)

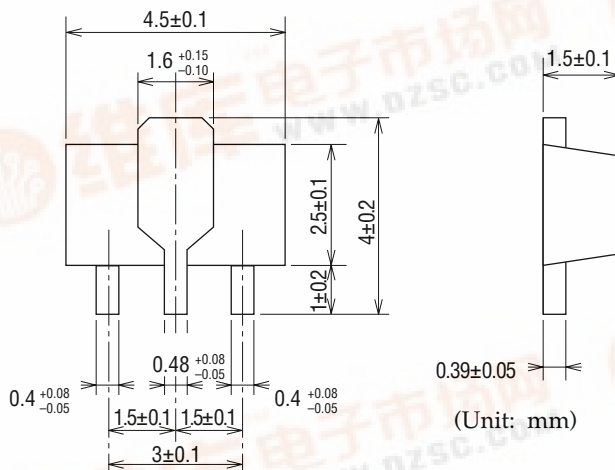
#### GENERAL DESCRIPTION

The KGF1284, housed in a SOT-89 type plastic-mold package, is a discrete power FET with frequencies ranging from the UHF-to L-band. This device features high efficiency, high output power, and high gain. The KGF1284 specifications are guaranteed to a fixed matching circuit for 3.4 V and 1.9 GHz; external impedance-matching circuits are also required. Because of its high efficiency, high output power (more than 21.5 dBm), high gain, and plastic package, the KGF1284 is ideal as a transmitter-driver amplifier for personal handy phones, such as digital keying cordless phones.

#### FEATURES

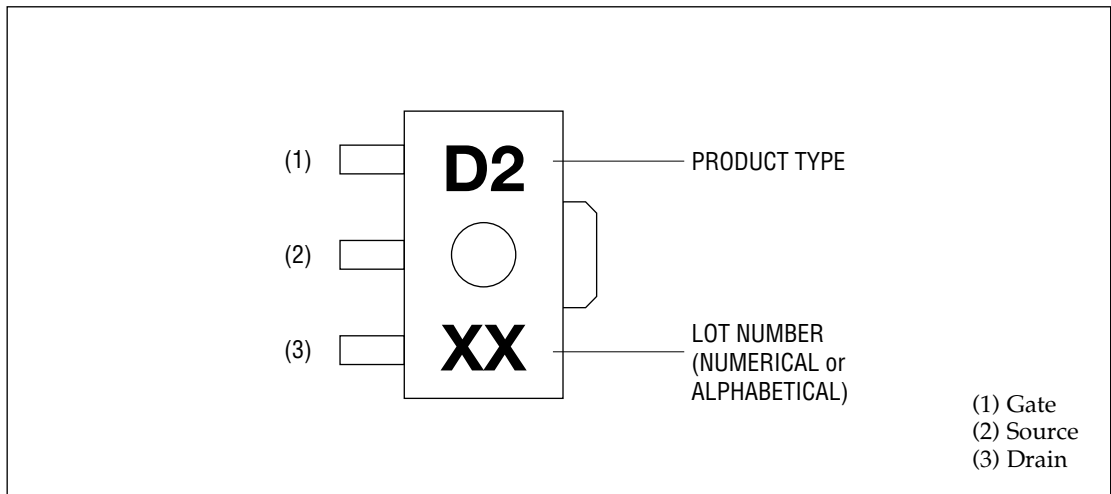
- Specifications guaranteed to a fixed matching circuit for 3.4 V, 1.9 GHz
- High output power: 21.5 dBm (min.) at 1.9 GHz
- High efficiency: 50% (typ.) at 1.9 GHz
- High linear gain: 12 dB (typ.) at 1.9 GHz
- Package: 3PMMP (SOT-89 type)

#### PACKAGE DIMENSIONS

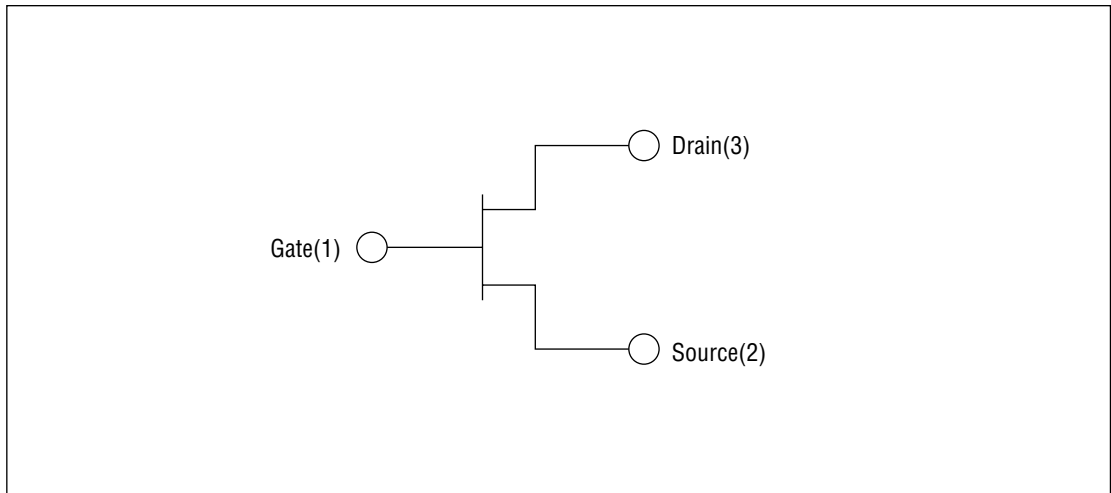


Package material	Epoxy resin
Lead frame material	Cu
Pin treatment	Solder plating
Solder plate thickness	5 $\mu$ m or more

### MARKING



### CIRCUIT



**ABSOLUTE MAXIMUM RATINGS**

Item	Symbol	Condition	Unit	Min.	Max.
Drain-source voltage	$V_{DS}$	$T_a = 25^\circ\text{C}$	V	—	7.0
Gate-source voltage	$V_{GS}$	$T_a = 25^\circ\text{C}$	V	-5.0	0.4
Drain current	$I_{DS}$	$T_a = 25^\circ\text{C}$	A	—	0.8
Total power dissipation	$P_{tot}$	$T_a = T_c = 25^\circ\text{C}$	W	—	2.5
Channel temperature	$T_{ch}$	—	$^\circ\text{C}$	—	150
Storage temperature	$T_{stg}$	—	$^\circ\text{C}$	-45	125

**ELECTRICAL CHARACTERISTICS**

(Ta = 25°C)

Item	Symbol	Condition	Unit	Min.	Typ.	Max.
Gate-source leakage current	$I_{GSS}$	$V_{GS} = -5\text{ V}$	$\mu\text{A}$	—	—	50
Gate-drain leakage current	$I_{GDO}$	$V_{GD} = -12\text{ V}$	$\mu\text{A}$	—	—	150
Drain-source leakage current	$I_{DS(off)}$	$V_{DS} = 7\text{ V}, V_{GS} = -5\text{ V}$	$\mu\text{A}$	—	—	500
Drain current	$I_{DSS}$	$V_{DS} = 1.5\text{ V}, V_{GS} = 0\text{ V}$	mA	450	—	—
Gate-source cut-off voltage	$V_{GS(off)}$	$V_{DS} = 3\text{ V}, I_{DS} = 1.4\text{ mA}$	V	-3.0	—	-2.0
Output power	$P_O$	(*1), $P_{IN} = 12\text{ dBm}$	dBm	21.5	22.5	—
Drain efficiency	$\eta_D$	(*1), $P_{IN} = 12\text{ dBm}$	%	45	50	—
Linear gain	$G_{LIN}$	(*1), $P_{IN} = -5\text{ dBm}$	dB	—	12.0	—
Thermal resistance	$R_{th}$	Channel to case	$^\circ\text{C/W}$	—	35	—

\*1 Condition:  $f = 1.9\text{ GHz}$ ,  $V_{DS} = 3.4\text{ V}$ ,  $I_{DSQ} = 70\text{ mA}$

RF CHARACTERISTICS

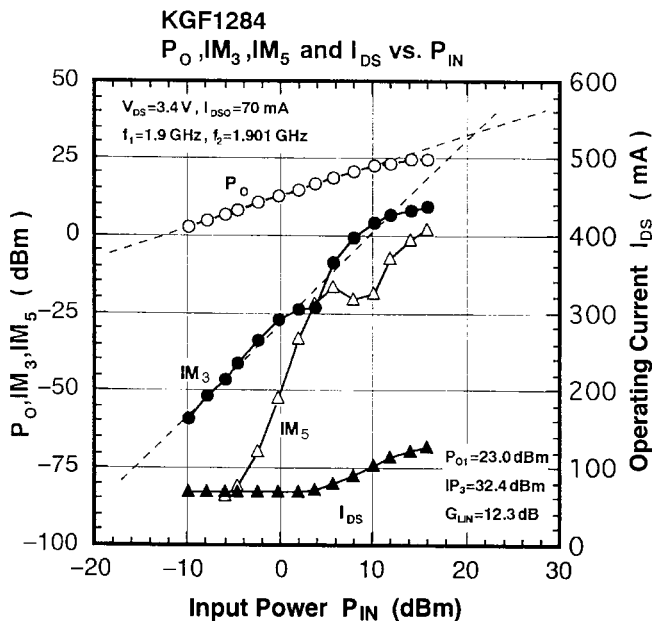
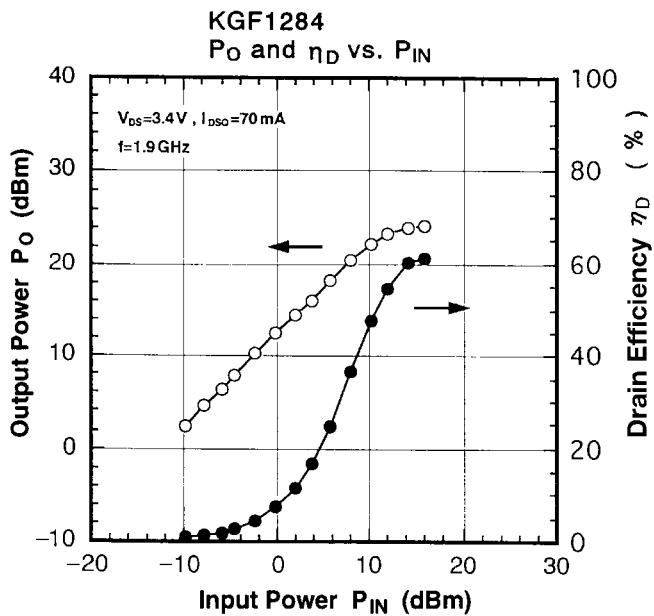
Matching conditions

Gamma S (Source impedance) :  $4.94 + j8.41 (\Omega)$

Gamma L (Load impedance) :  $16.28 + j2.61 (\Omega)$

Bias conditions

$V_{DS}=3.4V, I_{DSQ}=70mA, f=1.9Hz$

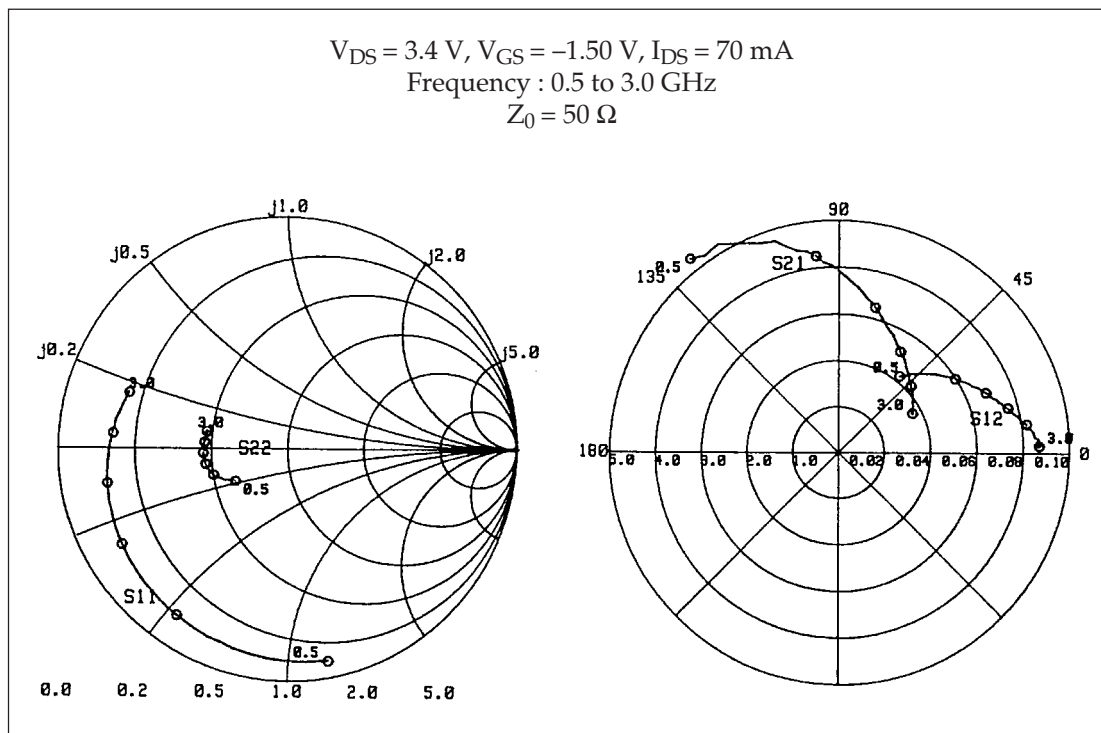


## Typical S Parameters

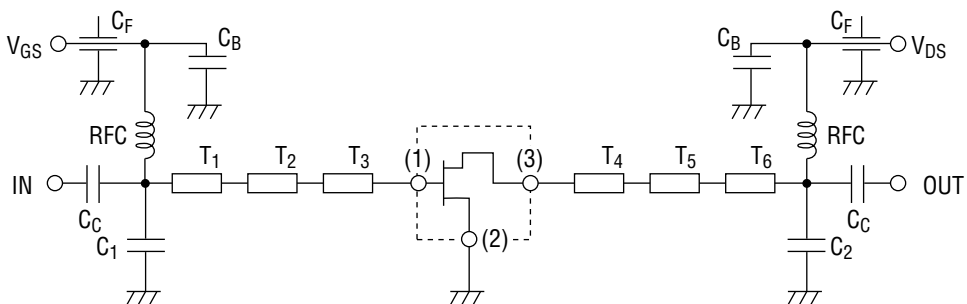
 $V_{DS} = 3.4\text{ V}$ ,  $V_{GS} = -1.50\text{ V}$ ,  $I_{DS} = 70\text{ mA}$ 

Freq(MHz)	MAG(S <sub>11</sub> )	ANG(S <sub>11</sub> )	MAG(S <sub>21</sub> )	ANG(S <sub>21</sub> )	MAG(S <sub>12</sub> )	ANG(S <sub>12</sub> )	MAG(S <sub>22</sub> )	ANG(S <sub>22</sub> )
500.0	0.929	-78.89	5.276	128.00	0.042	51.45	0.267	-148.33
600.0	0.912	-90.54	5.192	120.39	0.047	46.56	0.290	-151.44
700.0	0.898	-100.54	4.906	113.48	0.051	42.16	0.309	-153.97
800.0	0.883	-109.32	4.758	107.25	0.055	38.55	0.323	-156.56
900.0	0.876	-117.13	4.432	102.09	0.057	35.18	0.335	-158.61
1000.0	0.866	-123.86	4.255	96.87	0.060	32.38	0.343	-160.77
1100.0	0.859	-130.11	4.020	92.12	0.062	30.00	0.350	-162.66
1200.0	0.851	-135.65	3.790	87.84	0.064	27.73	0.355	-164.65
1300.0	0.844	-140.78	3.588	83.54	0.065	25.74	0.360	-166.30
1400.0	0.838	-145.60	3.381	79.70	0.067	23.56	0.363	-168.00
1500.0	0.832	-149.99	3.226	75.89	0.069	22.15	0.364	-169.53
1600.0	0.825	-154.26	3.066	72.32	0.070	20.26	0.366	-171.09
1700.0	0.819	-158.20	2.908	68.85	0.072	18.89	0.366	-172.68
1800.0	0.812	-161.99	2.809	65.26	0.073	17.33	0.369	-174.12
1900.0	0.806	-165.60	2.666	61.68	0.074	16.01	0.366	-175.62
2000.0	0.799	-169.02	2.570	58.72	0.076	14.72	0.369	-177.03
2100.0	0.793	-172.66	2.470	54.67	0.077	13.41	0.366	-178.53
2200.0	0.785	-175.81	2.367	52.14	0.078	12.04	0.367	179.93
2300.0	0.778	-178.99	2.285	48.53	0.080	10.71	0.365	178.65
2400.0	0.771	177.76	2.194	45.78	0.080	9.42	0.365	177.06
2500.0	0.764	174.95	2.129	42.86	0.082	8.56	0.364	175.54
2600.0	0.758	171.70	2.067	39.50	0.082	7.12	0.361	174.11
2700.0	0.750	168.79	1.991	36.47	0.085	5.91	0.360	172.44
2800.0	0.742	165.98	1.932	33.51	0.085	4.43	0.359	171.33
2900.0	0.736	163.16	1.854	30.44	0.087	2.92	0.358	169.80
3000.0	0.733	160.53	1.808	27.91	0.087	1.82	0.360	168.19

Typical S Parameters



Test Circuit and Bias Configuration for KGF1284 at 1.9 GHz



f = 1.9 GHz  
 T<sub>1</sub>: Z<sub>0</sub> = 80 Ω, E = 53 deg      T<sub>4</sub>: Z<sub>0</sub> = 30 Ω, E = 53 deg  
 T<sub>2</sub>: Z<sub>0</sub> = 10 Ω, E = 32 deg      T<sub>5</sub>: Z<sub>0</sub> = 12 Ω, E = 32 deg  
 T<sub>3</sub>: Z<sub>0</sub> = 30 Ω, E = 53 deg      T<sub>6</sub>: Z<sub>0</sub> = 50 Ω, E = 54 deg  
 C<sub>1</sub> = 1.0 pF, C<sub>2</sub> = 2.0 pF  
 C<sub>C</sub> = 1000 pF, C<sub>F</sub> = 1000 pF, C<sub>B</sub> = 1000 pF, RFC = 60 nH